

KSC1222

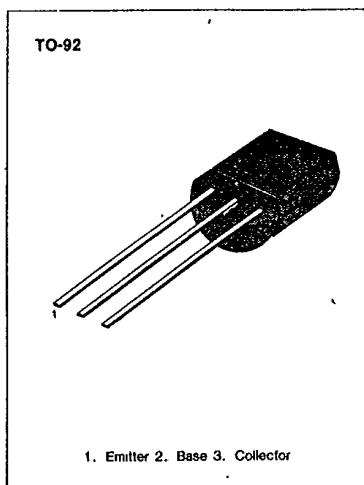
NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY LOW NOISE AMPLIFIER

- Collector-Base Voltage $V_{CB0} = 50V$
- Low Noise Level $NL = 40mV$ (Max)

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	50	V
Collector-Emitter Voltage	V_{CE0}	45	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	50	mA
Collector Dissipation	P_C	250	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ C$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = 100\mu A, I_E = 0$	50			V
Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_C = 10mA, I_B = 0$	45			V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E = -10\mu A, I_C = 0$	5			V
Collector Cut-off Current	I_{CB0}	$V_{CB} = 50V, I_E = 0$			50	nA
Emitter Cut-off Current	I_{EB0}	$V_{EB} = 5V, I_C = 0$			100	nA
DC Current Gain	h_{FE}	$V_{CE} = 3V, I_C = 0.5mA$	120		1000	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 2mA$		0.1	0.2	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = 3V, I_C = 0.5mA$		0.62	0.7	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = 3V, I_C = 1mA$	50	100		MHz
Noise Level	NL	$V_{CE} = 12V, I_E = -0.1mA$ $R_S = 25K\Omega$ $A_V = 80dB, (f = 1KHz)$		27	40	mV

h_{FE} CLASSIFICATION

Classification	Y	G	L	V
h_{FE}	120-240	200-400	350-700	600-1000

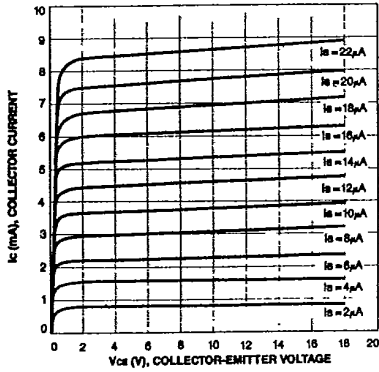


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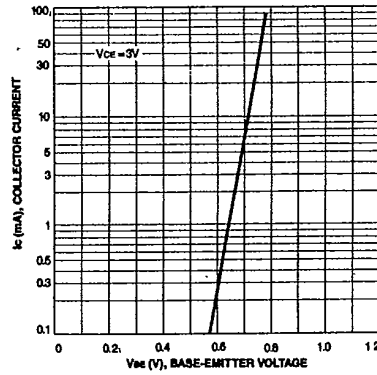
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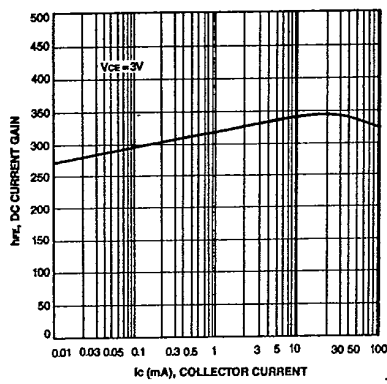
STATIC CHARACTERISTIC



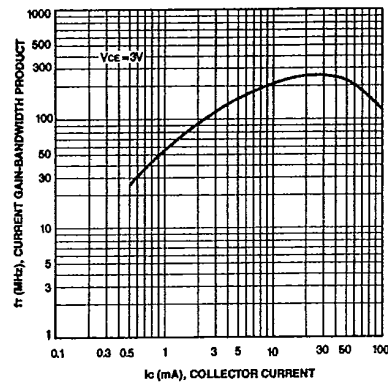
BASE-EMITTER ON VOLTAGE



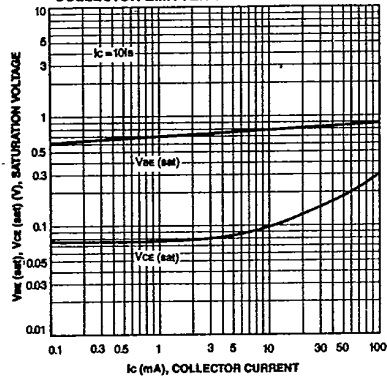
DC CURRENT GAIN



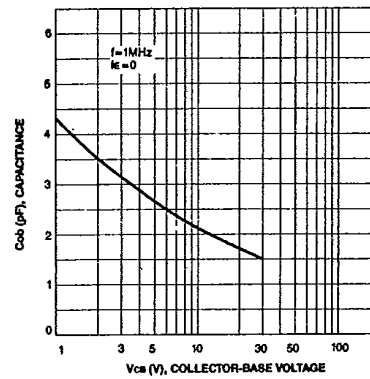
CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



OUTPUT CAPACITANCE



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